# FAIRCHILD

SEMICONDUCTOR®

# KSC2310

## **High Voltage Power Amplifier**

- Collector-Base Voltage : V<sub>CBO</sub>=200V
  Current Gain Bandwidth Product : f<sub>T</sub>=100MHz



# NPN Epitaxial Silicon Transistor

Absolute Maximum	<b>Ratings</b> $T_a=25^{\circ}C$ unless otherwise noted
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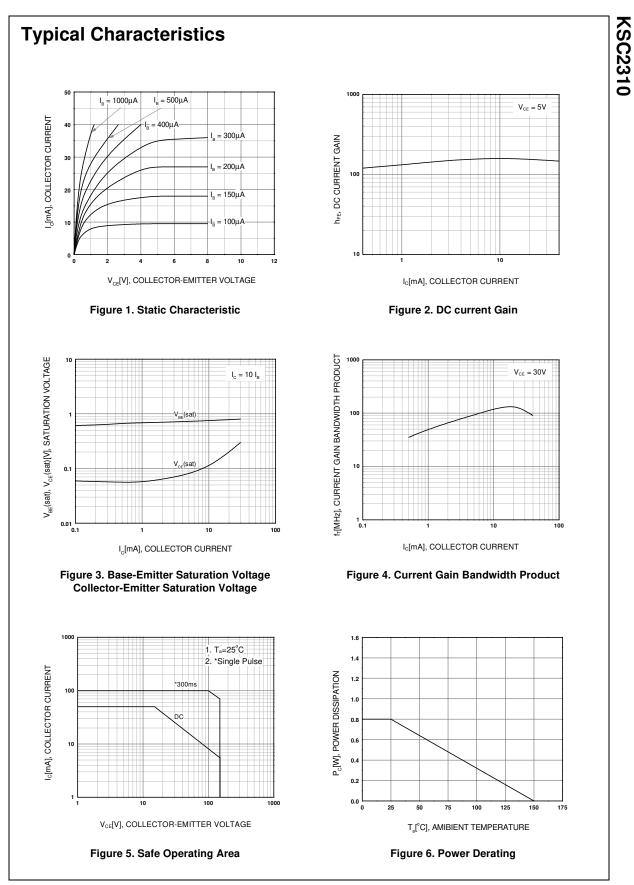
Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current	50	mA
P <sub>C</sub>	Collector Power Dissipation	800	mW
ТJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	200			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =5mA, I <sub>B</sub> =0	150			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =200V, I <sub>E</sub> =0			0.1	μA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	40		240	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.5	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =30V, I <sub>C</sub> =10mA		100		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		3.5	5	pF

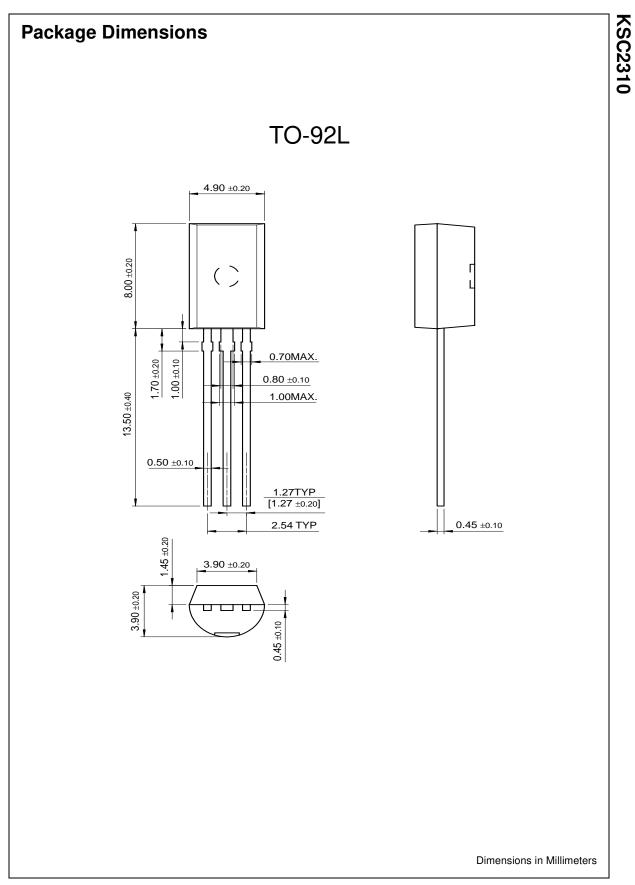
## h<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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